

**L830N-04E-35**

Infrared LED Lamp

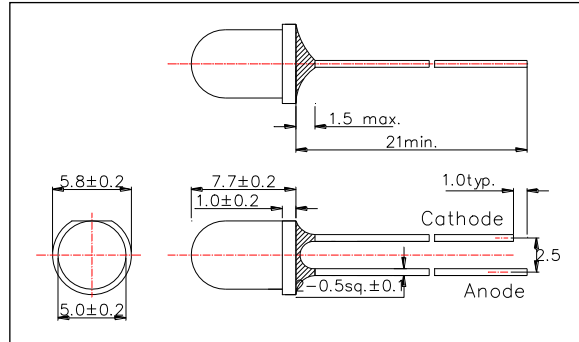
L830N-04E-35 is an AlGaAs LED mounted on a lead frame with a clear epoxy lens and is 48mW type of output power and 76mW/sr type of radiant intensity.

On forward bias, it emits a spectral band of radiation that peaks at 830nm.

<Specifications>

1. Product Name: Infrared LED Lamp
2. Type Number: L830N-04E-35
3. Chip:
  - Chip material: AlGaAs
  - Peak Wavelength: 830nm typ.
4. Package
  - Type: Φ5mm Clear Molding
  - Resin Material: Epoxy Resin
  - Lead Frame: Soldered(Lead Free)

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	180	mW
Forward Current	IF	100	mA
Pulse Forward Current*	IFP	500	mA
Reverse Voltage	VR	5	V
Junction Temperature	Tj	100	°C
Thermal Resistance**	Rthjp	240	K/W
Operating Temperature	TOPR	-40 ~ +85	°C
Storage Temperature	TSTG	-40 ~ +100	°C
Soldering Temperature***	TSOL	265	°C

\* Duty=1% and Pulse Width=10us.

\*\* Junction - ambient, leads 7mm, soldered on PCB

\*\*\* Soldering condition must be completed within 3 second at 265 °C.

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA DC		1.60	1.80	V
		IF=500mA, tp=10us		3.20	4.00	
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power*	PO	IF=50mA DC	18	24		mW
		IF=100mA, tp=20ms		48		
Radiant Intensity**	IE	IF=50mA DC	23	38		mcd
		IF=100mA, tp=20ms		76		
Peak Wavelength	λP	IF=50mA	815	830	845	nm
Half Width	Δλ	IF=50mA		35		nm
Viewing Half Angle	θ1/2	IF=50mA		±18		deg
Rise Time	Tr	IF=50mA		20		ns
Fall Time	tf	IF=50mA		15		ns

\* Measured by Photodyne #500

\*\* Measured by Tektronix J-6512

